

Docket No.: P2001,0176

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By: 

Date: October 1, 2003

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applic. No. : 10/657,841  
Applicant : Johannes Baur et al.  
Filed : September 9, 2003  
Art Unit : to be assigned  
Examiner : to be assigned

Docket No. : P2001,0176  
Customer No. : 24131

### INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner for Patents

Sir:

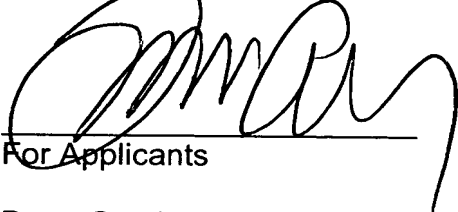
In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are submitted herewith:

Japanese Patent Abstract JP 61 110 476 (Yanagihara), dated May 28, 1986;

J. Zhang et al.: "Precise microfabrication of wide band gap semiconductors (SiC and GaN) by VUV-UV multiwavelength laser ablation", *Applied Surface Science*, Vol. 127-129, 1998, pp. 793-799;

W. N. Carr: "Photometric Figures Of Merit For Semiconductor Luminescent Sources Operating in Spontaneous Mode", *Infrared Physics*, 1966, Vol. 6, pp. 1-19.

Respectfully submitted,

  
For Applicants

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FORM PTO-1449 (SUBSTITUTE)

U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE

Attorney Docket No.:

P2001,0176

Applic. No.

10/657,841

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Johannes Baur et al.

Filing Date

September 9, 2003

Group Art Unit

INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT  
(37 CFR 1.98(b))

## U.S. PATENT DOCUMENTS

EXAMINER INITIALS		PATENT NO.	DATE	PATENTEE	CLASS	SUB CLASS	FILING DATE
	A						
	B						
	C						
	D						
	E						
	F						
	G						
	H						
	I						

## FOREIGN PATENT DOCUMENT

		DOCUMENT NO.	DATE	COUNTRY	CLASS	SUB CLASS	TRANSL. YES   NO
	J	61 110 476	05/28/86	Japan			X
	K						
	L						
	M						
	N						

## OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)

O	J. Zhang et al.: "Precise microfabrication of wide band gap semiconductors (SiC and GaN) by VUV-UV multiwavelength laser ablation", <i>Applied Surface Science</i> , Vol. 127-129, 1998, pp. 793-799
P	W. N. Carr: "Photometric Figures Of Merit For Semiconductor Luminescent Sources Operating in Spontaneous Mode", <i>Infrared Physics</i> , 1966, Vol. 6, pp. 1-19

EXAMINER

DATE CONSIDERED

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.